Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-244-8470

Inclos	sure Material:
Glass	and metal
Overa	II Length:
0.210	inches
Termi	nal Length:
0.500	inches
Overa	II Diameter:
0.230	inches
Intern	al Configuration:
Juncti	on contact
Moun	ting Method:
Termi	nal
Termi	nal Circle Diameter:
0.100	inches
Featu	res Provided:
Herme	etically sealed case
Semio	conductor Material:
Silicor	1
Volta	ge Rating In Volts Per Characteristic:
5.0 re	everse gate to source voltage
Curre	nt Rating Per Characteristic:
250.0	D milliamperes on-state current, average
Powe	r Rating Per Characteristic:
0.42 v	vatts peak gate power-forward
Maxin	num Operating Tempurature Per Measurement Point:
100.0	degrees celsius ambient air
Speci	al Features:
Juncti	on pattern arrangement: pnpn
Precie	ous Material And Location:
Termi	nal surfaces gold
Precie	ous Material:
Gold	
Termi	nal Type And Quantity:
3 unin	sulated wire lead
Shelf	Life:
N/a	
Unit C	Df Measure:
Demil	itarization:
No	
Fiig:	
A110a	a0